

## ABSTRACT

An object to be processed has a chromium-based thin film made of a  
5 material containing chromium. The thin film is etched using a resist pattern as a  
mask. The thin film is etched by the use of a chemical species produced by  
preparing a dry etching gas containing a halogen-containing gas and an  
oxygen-containing gas and supplying a plasma excitation power to the dry  
etching gas to thereby excite plasma. The thin film is etched using, as the  
10 plasma excitation power, a power lower than a plasma excitation power at which  
plasma density jump occurs.